

Customer No.: 31561  
Docket No.: 13137-US-PA  
Application No.: 10/710,844

### AMENDMENTS

#### To the Claims:

Claim 1. (previously presented) A low-temperature polysilicon thin film transistor (LTPS-TFT), adapted to be disposed on a substrate, the LTPS-TFT comprising:

- a gate disposed on the substrate;
- a gate dielectric layer disposed on the substrate and the gate;
- a patterned silicon layer disposed on the gate dielectric layer and over the gate, wherein the patterned silicon layer comprises a polysilicon channel region and an amorphous silicon hot carrier restrain region adjacent thereto;
- a patterned insulating layer disposed on the patterned silicon layer;
- an ohmic contact layer disposed on a portion of the patterned silicon layer other than the polysilicon channel region and the amorphous silicon hot carrier restrain region as well as a portion of the insulating layer over the amorphous silicon hot carrier restrain region to expose a portion of the patterned insulating layer; and
- a source/drain layer disposed on the ohmic contact layer.

Claim 2. (original) The LTPS-TFT of claim 1, further comprising a passivation layer disposed on the source/drain layer to cover the patterned insulating layer.

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Claim 3. (original) The LTPS-TFT of claim 1, wherein the ohmic contact layer comprises an n-type ohmic contact layer or a p-type ohmic contact layer.

Claim 4. (original) The LTPS-TFT of claim 1, wherein the material of the insulating layer comprises silicon oxide or silicon nitride.

Claims 5-19 (cancelled)

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